

Form PTO-1449 (modified)	Atty. Docket No. 2000.111200/H2022	Serial No. <del>Unknown</del> 10/664 665
List of Patents and Publications for Applicant's  INFORMATION DISCLOSURE STATEMENT  (Use several sheets if necessary)	Applicant Akram Ali Salman, Xuejun Zhao, Kurt O. Taylor and Stephen G. Beebe	
	Filing Date: September 18, 2003	Group: <del>Unknown</del> 2813
U.S. Patent Documents See Page 1	Foreign Patent Documents See Page 1	Other Art See Page 1

## U.S. Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Name	Class	Sub Class	Filing Date of App.
	A1						
	A2						
	A3						

## Foreign Patent Documents

Exam. Init.	Ref. Des.	Document Number	Date	Country	Class	Sub Class	Translation Yes/No
	B1						
	B2						
	B3						

## Other Art (Including Author, Title, Date Pertinent Pages, Etc.)

Exam. Init.	Ref. Des.	Citation
<i>AS</i>	C1	Salman <i>et al.</i> , "Gate Dielectric Breakdown and Latent Failures of Ultrathin (~13A) DPN under Pulsed Stress in Partially Depleted SOI MOSFETs"
<i>AS</i>	C2	Wu <i>et al.</i> , "Breakdown and Latent Damage of Ultra-Thin Gate Oxides under ESD Stress Conditions," EOS/ESD Symposium 00-287-295
<i>AS</i>	C3	Montoya <i>et al.</i> , "A Study of the Mechanisms for ESD Damage to Reticles," EOS/ESD Symposium 00-394-405
<i>AS</i>	C4	Hunter, "The Analysis of Oxide Reliability Data," 98 IRW Final Report, 114-34
<i>AS</i>	C5	Linder <i>et al.</i> , "Growth and Scaling of Oxide Conduction after Breakdown," 2003 IEEE, 402-05
<i>AS</i>	C6	Alam and Smith, "A Phenomenological Theory of Correlated Multiple Soft-Breakdown Events in Ultra-Thin Gate Dielectrics," 2003 IEEE, 406-411

EXAMINER:

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DATE CONSIDERED:

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